505268608 01/08/2019

PATENT ASSIGNMENT COVER SHEET

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SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
Hsiao-Pang Chou	01/04/2019
Hon-Huei Liu	01/04/2019
Ming-Chang Lu	01/04/2019
Chin-Fu Lin	01/04/2019
Yu-Cheng Tung	01/04/2019

RECEIVING PARTY DATA

Name:	UNITED MICROELECTRONICS CORP.
Street Address:	No.3, Li-Hsin Road 2, Science-Based Industrial Park
City:	Hsin-Chu City
State/Country:	TAIWAN

PROPERTY NUMBERS Total: 1

Property Type	Number
Application Number:	16242994

CORRESPONDENCE DATA

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ATTORNEY DOCKET NUMBER:	NAUP3376USA
NAME OF SUBMITTER:	SIBYL YU
SIGNATURE:	/SIBYL YU/
DATE SIGNED:	01/08/2019

Total Attachments: 10 source=3359969#page1.tif source=3359969#page2.tif source=3359969#page3.tif



Title of Invention:

SEMICONDUCTOR STRUCTURE WITH AN EPITAXIAL LAYER AND METHOD OF MANUFACTURING THE SAME

As the below named inventor, I here This declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application nu	mber	_filed on	, or
☐ PCT international application	number	filed on	
The above-identified application was	made or authorized to be made	by me.	
I believe that I am the original invent application.	or or an original joint inventor of a	ı claimed invention ir	n the
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In consideration of the payment by	UNITED MICROELECTRON CORP.	NICS having a po	ostal address of
No.3, Li-Hsin Road 2, Science	e-Based Industrial Park, Hsi	in-Chu City 300,	Taiwan, R.O.C
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an		00), the receipt of wh	ich is hereby
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I hereby covenant that no assignment entered into which would conflict with		nce has been or will l	be made or
I further covenant that ASSIGNEE w and documents relating to said inver known and accessible to I and will te related thereto and will promptly exe	ntion and said Letters Patent and estify as to the same in any interfe	legal equivalents as rence, litigation proc	may be
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Note: An application data sheet (PTC	D/SB/14 or equivalent), including	naming the entire	

Page 1 of 10

inventive entity, must accompany this form. Use this form for each additional inventor.

NPO#NAU-P3376-USA:0 CUST#UMCD-2018-0447

Inventor: Hsiao-Pang Chou Date: JAN 0 4 2019

Signature:

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NPO#NAU-P3376-USA:0 CUST#UMCD-2018-0447

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I hereby sell, assign and transfer to a the entire right, title and interest in a invention as above-identified applica invention by the above application of substitutes, or extensions thereof, an	nd to any and all improvements of tion and, in and to, all Letters Pa r any continuations, continuation	which are disclose atent to be obtained i-in-part, divisions,	d in the d for said renewals,
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NPO#NAU-P3376-USA:0 CUST#UMCD-2018-0447

LEGAL NAI	ME OF INVENTOR(ASSIGNOR)		
Inventor:	Hon-Huei Liu	Date:	JAN 0 4 2019
Signature:	ldon ldur X-		

NPO#NAU-P3376-USA:0 CUST#UMCD-2018-0447 Page 4 of 10

F#NPO-P0002E-US1201 DSB0-107U031292

Title of Invention:

SEMICONDUCTOR STRUCTURE WITH AN EPITAXIAL LAYER AND METHOD OF MANUFACTURING THE SAME

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Note: An application data sheet (PTC inventive entity, must accompany thi	O/SB/14 or equivalent), including i s form. Use this form for each add	naming the entire ditional inventor.	

Page 5 of 10

NPO#NAU-P3376-USA:0 CUST#UMCD-2018-0447

Inventor:	Ming-Chang Lu		Date:	JAN 0 4 2019	
Signature:	Mrng-Chang L	» W.	***************************************	JA	_
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F#NPO-P0002E-US1201 DSB0-107U031292

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NPO#NAU-P3376-USA:0 CUST#UMCD-2018-0447

nventor:	Chin-Fu Lin		Date:	JAN 0 4 2	019	
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F#NPO-P0002E-US1201 DSB0-107U031292

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Page 9 of 10

NPO#NAU-P3376-USA:0 CUST#UMCD-2018-0447

Inventor:	Yu-Cheng Tung		Date:	JAN 0	4 2019	
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